

**Amendments to the Specification:**

Kindly replace paragraph 0032 with the following paragraph:

Fig. 2B is a cross-section along line A-A' in Fig. 2A illustrating the formation of fin structure 210 in accordance with an exemplary embodiment of the present invention. As described above, dielectric layer 140 and silicon layer 130 may be etched to form structure 210. Structure 210 may include a silicon fin 130 and a dielectric cap 140. In an exemplary implementation, the width of silicon fin 130 may range from [[about 10 Å to about 100 Å]] about 10 Å to about 100 Å.